

Claims 1-8 have been cancelled.

9. (Amended) A method of fabricating a semiconductor package, comprising:

- (a) preparing a lead frame that has a protrusion;
- (b) preparing a first molding die member having a cavity;
- (c) preparing a second molding die member to be engaged with the first molding die member;
- (d) disposing a substantially spherical terminal in the cavity;
- (e) holding the lead frame between the first and second molding die members such that the protrusion is disposed opposite to the substantially spherical terminal; and
- (f) a step of injecting a molding composition between the first and second molding die members.

10. (Amended) A method of fabricating a semiconductor package according to claim 9, wherein the substantially spherical terminal comes to be in intimate contact with the sidewall of the cavity in step (e).

11. (Amended) A method of fabricating a semiconductor package according to claim 9, wherein the protrusion has an extremity forming an acute angle, and wherein step (e) further comprises causing the protrusion to pierce the substantially spherical terminal.

12. (Amended) A method of fabricating a semiconductor package comprising:

- (a) preparing a lead frame that has a locally roughened face;
- (b) preparing a first molding die member having a cavity;
- (c) preparing a second molding die member to be engaged with the first molding die member;
- (d) disposing a substantially spherical terminal in the cavity;

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(e) holding the lead frame between the first and second molding die members such that the locally roughened face is disposed opposite to the substantially spherical terminal; and

(f) injecting a molding composition between the first and second molding die members,

wherein step (e) further comprises causing the locally roughened face to press against the substantially spherical terminal.

13. (Amended) A method of fabricating a semiconductor package according to claim 9, further comprising the step of sucking in the substantially spherical terminal via a through hole in the bottom of the cavity of the first molding die member.

14. (Amended) A method of forming a semiconductor package which comprises the steps of:

preparing a lead frame having a substantially spherical terminal;

preparing a first mold die having a cavity with a through hole in the bottom thereof;

preparing a second mold die for matching with said first molding die;

placing said lead frame between said first and second mold dies, wherein said substantially spherical terminal of said lead frame is placed in said cavity;

absorbing air existing between said substantially spherical terminal and said bottom of said cavity via said through hole to urge said substantially spherical terminal against the inner side of said cavity; and

injecting a molding composition between said first and second mold dies.

15. (Amended) A method of forming a semiconductor package which comprises the steps of:

preparing a lead frame having a substantially spherical terminal;

preparing a first mold die having a cavity with a through hole in the bottom thereof;

preparing a second mold die for matching with said first molding die;

placing said lead frame between said first and second mold dies, wherein said substantially spherical terminal of said lead frame is placed in said cavity;

bringing said first and second mold;

exposing a bottom portion of said substantially spherical terminal to reduced pressure via said through hole in the bottom of the cavity so as to urge said substantially spherical terminal against an inner side of said cavity; and

injecting a molding composition between said first and second mold dies.

16. (New) The method of fabricating a semiconductor package according to claim 11, wherein the step of causing the protrusion to pierce the substantially spherical terminal comprises pressing against the lead frame with a press-down part of the second molding die.

17. (New) The method of fabricating a semiconductor package according to claim 9, wherein the lead frame has a bottom side and the protrusion comprises a solder layer on a portion of the bottom side of the lead frame, and wherein step (e) further comprises causing the solder layer to press against the substantially spherical terminal.

18. (New) A method of fabricating a semiconductor package using a mold having upper and lower mold dies that are movable between an open state and a closed state, the mold dies defining a mold cavity when they are in their closed state, said method comprising:

(a) while the mold dies are in their open state, placing a solder ball in a recess of a lower molding die;

(b) while the mold dies are in their open state, placing a lead frame above the lower molding die, with the lead frame having a lead that passes over the solder ball, the lead having a bottom side with a downwardly extending protrusion;

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(c) moving the mold dies to their closed state, and simultaneously pressing the protrusion against the solder ball by pressing a hold-down part of the upper mold die against the lead, the hold-down part being located over the solder ball; and

(d) injecting a molding composition into the mold cavity.

19. (New) A method of fabricating a semiconductor package according to claim 18, wherein the protrusion is elongated in a downward direction, and is driven into the solder ball as step (c) is being conducted.

20. (New) A method of fabricating a semiconductor package according to claim 18, wherein the protrusion is a small solder layer that is pressed against the solder ball during step (c).

21. (New) A method of fabricating a semiconductor package according to claim 18, wherein the lower mold die has a passage that communicates with the recess, and further comprising the step of exposing the solder ball to reduced pressure via the passage so as to urge the solder ball tightly into the recess.

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